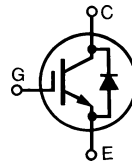


# IGBT with Diode ISOPLUS247™ (Electrically Isolated Backside)

Short Circuit SOA Capability

## IXSR 40N60CD1

$V_{CES} = 600 \text{ V}$   
 $I_{C25} = 62 \text{ A}$   
 $V_{CE(SAT)} = 2.5 \text{ V}$   
 $t_{fi(typ)} = 70 \text{ ns}$

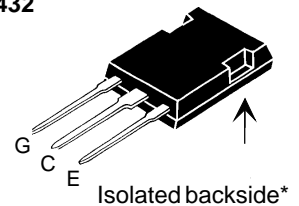


Preliminary data

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	600	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GE} = 1 \text{ M}\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$ , limited by leads	62	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	37	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1 ms	150	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15 \text{ V}$ , $T_{VJ} = 125^\circ\text{C}$ , $R_G = 22 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 80$ @ $0.8 V_{CES}$	A
<b><math>t_{SC}</math> (SCSOA)</b>	$V_{GE} = 15 \text{ V}$ , $V_{CE} = 360 \text{ V}$ , $T_J = 125^\circ\text{C}$ $R_G = 22 \Omega$ , non repetitive	10	$\mu\text{s}$
$P_C$	$T_C = 25^\circ\text{C}$	210	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS $t = 1 \text{ min}$	2500	V~
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
<b>Weight</b>	PLUS247	5	g

ISOPLUS 247™ (IXSR)

E 153432



G = Gate, C = Collector,  
E = Emitter

\* Patent pending

### Features

- DCB Isolated mounting tab
- Meets TO-247AD package Outline
- High current handling capability
- Latest generation HDMOS™ process
- MOS Gate turn-on - drive simplicity

### Applications

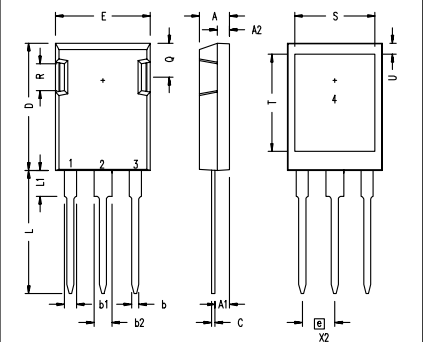
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

### Advantages

- Easy assembly
- High power density
- Very fast switching speeds for high frequency applications

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_C = 1 \text{ mA}$ , $V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 4 \text{ mA}$ , $V_{CE} = V_{GE}$	4		V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$ $T_J = 150^\circ\text{C}$			650 $\mu\text{A}$ 5 mA
$I_{GES}$	$V_{CE} = 0 \text{ V}$ , $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_T$ , $V_{GE} = 15 \text{ V}$			2.5 V

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$I_C = I_T; V_{CE} = 10\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $\leq 2\%$	16	23	S
$C_{ies}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		3700	pF
$C_{oes}$			440	pF
$C_{res}$			60	pF
$Q_g$	$I_C = I_T, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		190	nC
$Q_{ge}$			45	nC
$Q_{gc}$			88	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b>		50	ns
$t_{ri}$	$I_C = I_T, V_{GE} = 15\text{ V}, L = 100\ \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 2.7\ \Omega$		50	ns
$t_{d(off)}$			70	140 ns
$t_{fi}$	Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		70	120 ns
$E_{off}$			1.0	1.7 mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b>		50	ns
$t_{ri}$	$I_C = I_T, V_{GE} = 15\text{ V}, L = 100\ \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 2.7\ \Omega$		50	ns
$E_{on}$			2.2	mJ
$t_{d(off)}$	Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		140	ns
$t_{fi}$			140	ns
$E_{off}$			1.7	mJ
$R_{thJC}$				0.6 K/W
$R_{thCK}$		0.15		K/W

**ISOPLUS 247 (IXSR) OUTLINE**


1 Gate, 2 Drain (Collector)  
3 Source (Emitter)  
4 no connection

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190
S	13.21	13.72	.520	.540
T	15.75	16.26	.620	.640
U	1.65	3.03	.065	.080

**Reverse Diode (FRED)**

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_F$	$I_F = I_T, V_{GE} = 0\text{ V}$ , Pulse test $\leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.8 V
$I_{RM}$	$I_F = I_T, V_{GE} = 0\text{ V}, -di_F/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$ $I_F = 1\text{ A}; -di/dt = 200\text{ A}/\mu\text{s}; V_R = 30\text{ V}$		2	2.5 A
$t_{rr}$			35	ns
$R_{thJC}$				1.15 K/W

Note: 1.  $I_T = 40\text{ A}$